

Standard Rectifier

 $V_{RRM} = 2x \, 1600 \, V$

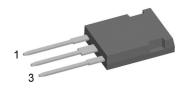
 $I_{EAV} = 45 A$

 $V_{F} = 1.23 V$

Phase leg

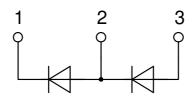
Part number

DSP45-16AR



Backside: isolated





Features / Advantages:

- Planar passivated chips
- Very low leakage currentVery low forward voltage drop
- Improved thermal behaviour

Applications:

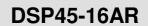
- Diode for main rectification
- For single and three phase bridge configurations

Package: ISOPLUS247

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

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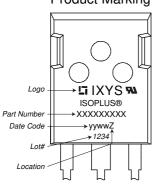


Rectifier					Ratings	S	
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse bloc	cking voltage	$T_{VJ} = 25^{\circ}C$			1700	V
V _{RRM}	max. repetitive reverse blocking	voltage	$T_{VJ} = 25^{\circ}C$			1600	٧
I _R	reverse current	V _R = 1600 V	$T_{VJ} = 25^{\circ}C$			40	μΑ
		$V_R = 1600 \text{ V}$	$T_{VJ} = 150$ °C			1.5	mΑ
V _F	forward voltage drop	I _F = 45 A	$T_{VJ} = 25^{\circ}C$			1.26	V
		$I_F = 90 A$				1.57	٧
		$I_F = 45 \text{ A}$	$T_{VJ} = 150 ^{\circ}\text{C}$			1.23	V
		$I_F = 90 A$				1.66	٧
I FAV	average forward current	T _C = 100°C	T _{vJ} = 175°C			45	Α
		180° sine					
V _{F0}	threshold voltage	deservation and	T _{vJ} = 175°C			0.81	V
\mathbf{r}_{F}	slope resistance	loss calculation only				9.1	mΩ
R _{thJC}	thermal resistance junction to ca	ase				0.9	K/W
R _{thCH}	thermal resistance case to heats	sink			0.3		K/W
P _{tot}	total power dissipation		$T_{C} = 25^{\circ}C$			165	W
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			480	Α
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			520	Α
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150$ °C			410	Α
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			440	Α
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			1.15	kA2s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			1.13	kA2s
		t = 10 ms; (50 Hz), sine	T _{vJ} = 150°C			840	A ² s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			805	A²s
C	junction capacitance	$V_{R} = 400 \text{ V}; f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		18		pF



Package	ISOPLUS247			ı	Ratings	S	
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal				70	Α
T _{VJ}	virtual junction temperature	-40		175	°C		
T _{op}	operation temperature					150	°C
T _{stg}	storage temperature			-40		150	°C
Weight					6		g
F _c	mounting force with clip			20		120	N
$d_{\text{Spp/App}}$	creepage distance on surface striking distance through all		2.7			mm	
$d_{Spb/Apb}$			terminal to backside	4.1			mm
V _{ISOL}	isolation voltage	t = 1 second	50/00 II	3600			٧
		t = 1 minute	50/60 Hz, RMS; lisoL ≤ 1 mA				٧

Product Marking



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.	
Standard	DSP45-16AR	DSP45-16AR	Tube	30	496561	

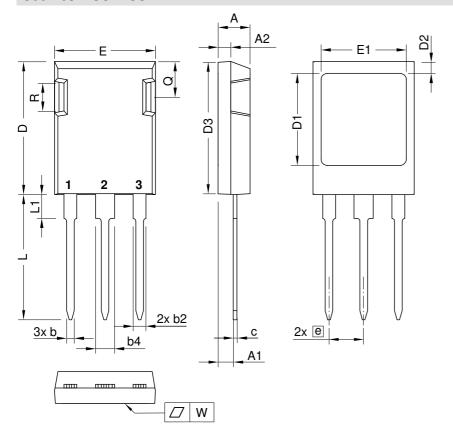
Similar Part	Package	Voltage class		
DSP45-16A	TO-247AD (3)	1600		
DSP45-16AZ	TO-268AA (D3Pak) (2HV)	1600		
DSP45-12A	TO-247AD (3)	1200		
DSP45-12AZ	TO-268AA (D3Pak) (2HV)	1200		

DSP45-18A	TO-247AD (3)	1800

Equiva	alent Circuits for	Simulation	* on die level	$T_{VJ} = 175^{\circ}C$
$I \rightarrow V_0$)—[R ₀]-	Rectifier		
V _{0 max}	threshold voltage	0.81		V
$R_{0 \text{ max}}$	slope resistance *	6.5		$m\Omega$



Outlines ISOPLUS247



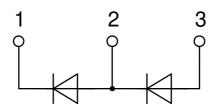
Dim.	Millir	neter	Inc	hes
Diiii.	min	max	min	max
Α	4.83	5.21	0.190	0.205
A1	2.29	2.54	0.090	0.100
A2	1.91	2.16	0.075	0.085
b	1.14	1.40	0.045	0.055
b2	1.91	2.20	0.075	0.087
b4	2.92	3.24	0.115	0.128
С	0.61	0.83	0.024	0.033
D	20.80	21.34	0.819	0.840
D1	15.75	16.26	0.620	0.640
D2	1.65	2.15	0.065	0.085
D3	20.30	20.70	0.799	0.815
Е	15.75	16.13	0.620	0.635
E1	13.21	13.72	0.520	0.540
е	5.45	BSC	0.215	BSC
L	19.81	20.60	0.780	0.811
L1	3.81	4.38	0.150	0.172
Q	5.59	6.20	0.220	0.244
R	4.25	5.50	0.167	0.217
W	-	0.10	-	0.004

Die konvexe Form des Substrates ist typ. < 0.04 mm über der Kunststoffoberfläche der Bauteilunterseite

The convex bow of substrate is typ. < 0.04 mm over plastic surface level of device bottom side

Die Gehäuseabmessungen entsprechen dem Typ TO-247 AD

gemäß JEDEC außer Schraubloch und L_{max}. This drawing will meet all dimensions requiarement of JEDEC outline TO-247 AD except screw hole and except L_{max}.





Rectifier

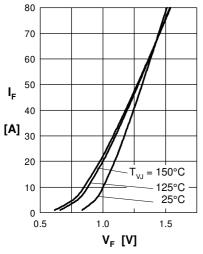


Fig. 1 Forward current versus voltage drop per diode

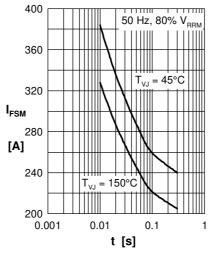


Fig. 2 Surge overload current

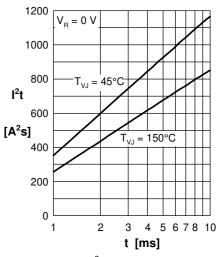


Fig. 3 I²t versus time per diode

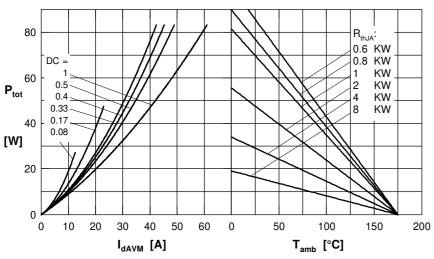


Fig. 4 Power dissipation vs. direct output current & ambient temperature

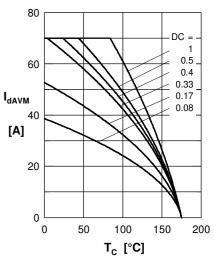


Fig. 5 Max. forward current vs. case temperature

1.0																	
0.8									1	T							
						\parallel											
Z _{th} 0.6																	
[K/W]																	
0.4			H														
0.4																	
0.2																	
0.2																	
0.0																	
0.0	1		1	10				00			1	00	00		1	00	000
						t	[ms]									

Fig. 6 Transient thermal impedance junction to case

i	Ri	ti
1	0.0607	0.0004
2	0.123	0.00256
3	0.2305	0.045
4	0.323	0.0242
5	0.1628	0.18